

FAST CMOS OCTAL BIDIRECTIONAL TRANSCEIVER

IDT54/74FCT245T/AT/CT

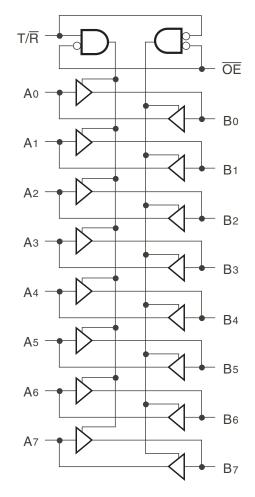
FEATURES:

- · Std., A, and C grades
- Low input and output leakage ≤1µA (max.)
- CMOS power levels
- · True TTL input and output compatibility:
 - VOH = 3.3V (typ.)
 - -VOL = 0.3V(typ.)
- High Drive outputs (-15mA IOH, 64mA IOL)
- · Meets or exceeds JEDEC standard 18 specifications
- Military product compliant to MIL-STD-883, Class B and DESC listed (dual marked)
- · Power off disable outputs permit "live insertion"
- Available in the following packages:
- Industrial: SOIC, SSOP, QSOP, TSSOP
- Military: CERDIP, LCC

FUNCTIONAL BLOCK DIAGRAM

DESCRIPTION:

The IDT octal bidirectional transceivers are built using an advanced dual metal CMOS technology. The FCT245T is designed for asynchronous twoway communication between data buses. The transmit/receive (T/\overline{R}) input determines the direction of data flow through the bidirectional transceiver. Transmit (active high) enables data from A ports to B ports, and receive (active low) from B ports to A ports. The output enable (\overline{OE}) input, when high, disables both A and B ports by placing them in high Z condition.

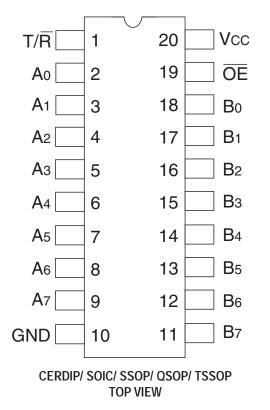


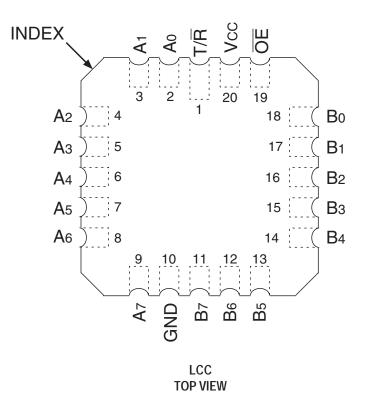
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MILITARY AND INDUSTRIAL TEMPERATURE RANGES

DECEMBER 2016

PINCONFIGURATION





ABSOLUTE MAXIMUM RATINGS⁽¹⁾

Symbol	Description	Max	Unit
VTERM ⁽²⁾	Terminal Voltage with Respect to GND	–0.5 to +7	V
VTERM ⁽³⁾	Terminal Voltage with Respect to GND	-0.5 to Vcc+0.5	V
Tstg	Storage Temperature	-65 to +150	°C
Ιουτ	DC Output Current	-60 to +120	mA

NOTES:

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability. No terminal voltage may exceed Vcc by +0.5V unless otherwise noted.
- 2. Inputs and Vcc terminals only.
- 3. Output and I/O terminals only.

CAPACITANCE (TA = +25°C, F = 1.0MHz)

Symbol	Parameter ⁽¹⁾	Conditions	Тур.	Max.	Unit
CIN	Input Capacitance	VIN = 0V	6	10	рF
Соит	Output Capacitance	Vout = 0V	8	12	pF

NOTE:

1. This parameter is measured at characterization but not tested.

PINDESCRIPTION

Pin Names	Description			
ŌĒ	Output Enable Inputs (Active LOW)			
T/R	Transmit/Recieve Input			
A0 - A7	Ao - A7 Side A Inputs or 3-State Outputs			
Bo - B7	B0 - B7 Side B Inputs or 3-State Outputs			

FUNCTION TABLE⁽¹⁾

Inp	uts	
ŌĒ	T/R	Outputs
L	L	Bus B Data to Bus A
L	Н	Bus A Data to Bus B
Н	Х	High Z State

NOTE:

1. H = HIGH Voltage Level

- X = Don't Care
- L = LOW Voltage Level

Z = High Impedance

DC ELECTRICAL CHARACTERISTICS OVER OPERATING RANGE

Following Conditions Apply Unless Otherwise Specified:

Industrial: TA = -40° C to $+85^{\circ}$ C, Vcc = 5.0V $\pm 5\%$; Military: TA = -55° C to $+125^{\circ}$ C, Vcc = 5.0V $\pm 10\%$

Symbol	Parameter	Test	t Conditions ⁽¹⁾	Min.	Тур. ⁽²⁾	Max.	Unit
Vih	Input HIGH Level	Guaranteed Logic HIGH L	evel	2	—	_	V
Vil	Input LOW Level	Guaranteed Logic LOW Le	evel	_	_	0.8	V
Ін	Input HIGH Current ⁽⁴⁾	Vcc = Max.	VI = 2.7V	_	_	±1	μA
lil	Input LOW Current ⁽⁴⁾	Vcc = Max.	VI = 0.5V	_	_	±1	μA
Іоzн	High Impedance Output Current	Vcc = Max	Vo = 2.7V	_	_	±1	μA
Iozl	(3-State output pins) ⁽⁴⁾		Vo = 0.5V		_	±1	
li	Input HIGH Current ⁽⁴⁾	Vcc = Max., VI = Vcc (Ma	ax.)	_	_	±1	μA
Vik	Clamp Diode Voltage	VCC = Min, IIN = -18mA		—	-0.7	-1.2	V
Vн	Input Hysteresis	—		-	200	_	mV
lcc	Quiescent Power Supply Current	VCC = Max., VIN = GND C	or Vcc	-	0.01	1	mA

OUTPUT DRIVE CHARACTERISTICS

Symbol	Parameter	Test Conditions ⁽¹⁾			Typ. ⁽²⁾	Max.	Unit
Vон	Output HIGH Voltage	Vcc = Min	Iон = –6mA MIL	2.4	3.3	-	
		VIN = VIH OF VIL	Iон = -8mA IND				V
			Iон = –12mA MIL	2	3	_	
			Iон = -15mA IND				
Vol	Output LOW Voltage	Vcc = Min	Iol = 48mA MIL	_	0.3	0.55	V
		VIN = VIH OF VIL	Iol = 64mA IND				
los	Short Circuit Current	Vcc = Max., Vo = GND ⁽³⁾		-60	-120	-225	mA

NOTES:

1. For conditions shown as Min. or Max., use appropriate value specified under Electrical Characteristics for the applicable device type.

2. Typical values are at Vcc = 5.0V, +25°C ambient.

3. Not more than one output should be tested at one time. Duration of the test should not exceed one second.

4. The test limit for this parameter is $\pm 5\mu A$ at TA = $-55^{\circ}C$.

POWER SUPPLY CHARACTERISTICS

Symbol	Parameter	Test Condition	ons ⁽¹⁾	Min.	Тур. ⁽²⁾	Max.	Unit
Δlcc	Quiescent Power Supply Current TTL Inputs HIGH	Vcc = Max. $VIN = 3.4V^{(3)}$		_	0.5	2	mA
ICCD	Dynamic Power Supply Current ⁽⁴⁾	Vcc = Max. Outputs Open OE = T/R = GND One Input Toggling 50% Duty Cycle	VIN = VCC VIN = GND	_	0.15	0.25	mA/ MHz
IC	Total Power Supply Current ⁽⁶⁾	Vcc = Max. Outputs Open fi = 10MHz	Vin = Vcc Vin = GND	—	1.5	3.5	mA
		50% Duty Cycle OE = T/R = GND One Bit Toggling	Vin = 3.4V Vin = GND	—	1.8	4.5	
		Vcc = Max. Outputs Open fi = 2.5MHz	Vin = Vcc Vin = GND	_	3	6(5)	
		50% Duty Cycle $\overline{OE} = T/\overline{R} = GND$ Eight Bits Toggling	Vin = 3.4V Vin = GND	—	5	14(5)	

NOTES:

1. For conditions shown as Min. or Max., use appropriate value specified under Electrical Characteristics for the applicable device type.

2. Typical values are at Vcc = 5.0V, +25°C ambient.

3. Per TTL driven input; (VIN = 3.4V). All other inputs at Vcc or GND.

4. This parameter is not directly testable, but is derived for use in Total Power Supply Calculations.

5. Values for these conditions are examples of Δ Icc formula. These limits are guaranteed but not tested.

6. IC = IQUIESCENT + INPUTS + IDYNAMIC

IC = ICC + Δ ICC DHNT + ICCD (fCP/2+ fiNi)

Icc = Quiescent Current

 ΔIcc = Power Supply Current for a TTL High Input (VIN = 3.4V)

DH = Duty Cycle for TTL Inputs High

NT = Number of TTL Inputs at DH

ICCD = Dynamic Current caused by an Input Transition Pair (HLH or LHL)

fcp = Clock Frequency for Register Devices (Zero for Non-Register Devices)

fi = Output Frequency

Ni = Number of Outputs at fi

All currents are in milliamps and all frequencies are in megahertz.

SWITCHING CHARACTERISTICS OVER OPERATING RANGE - INDUSTRIAL

			74FCT245AT 74FCT245CT		245CT		
Symbol	Parameter	Condition ⁽¹⁾	Min. ⁽²⁾	Max.	Min. ⁽²⁾	Max.	Unit
t PLH	Propagation Delay	CL = 50pF	1.5	4.6	1.5	4.1	ns
t PHL	A to B, B to A	RL = 500Ω					
tрzн	Output Enable Time		1.5	6.2	1.5	5.8	ns
tPZL	OE to A or B						
tphz	Output Disable Time		1.5	5	1.5	4.8	ns
tPLZ	OE to A or B						
tpzh	Output Enable Time		1.5	6.2	1.5	5.8	ns
tPZL	T/\overline{R} to A or $B^{(3)}$						
tphz	Output Disable Time		1.5	5	1.5	4.8	ns
tplz	T/\overline{R} to A or $B^{(3)}$						

SWITCHING CHARACTERISTICS OVER OPERATING RANGE - MILITARY

			54FCT245T		54FCT245AT 54FCT245CT		245CT		
Symbol	Parameter	Condition ⁽¹⁾	Min. ⁽²⁾	Max.	Min. ⁽²⁾	Max.	Min. ⁽²⁾	Max.	Unit
t PLH	Propagation Delay	CL = 50pF	1.5	7.5	1.5	4.9	1.5	4.5	ns
t PHL	A to B, B to A	$RL = 500\Omega$							
tpzh	Output Enable Time		1.5	10	1.5	6.5	1.5	6.2	ns
tPZL	OE to A or B								
t PHZ	Output Disable Time		1.5	10	1.5	6	1.5	5.2	ns
tPLZ	OE to A or B								
t PZH	Output Enable Time		1.5	10	1.5	6.5	1.5	6.2	ns
tPZL	T/R to A or B ⁽³⁾								
t PHZ	Output Disable Time		1.5	10	1.5	6	1.5	5.2	ns
tplz	T/\overline{R} to A or $B^{(3)}$								

NOTES:

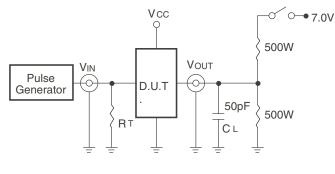
1. See test circuit and waveforms.

2. Minimum limits are guaranteed but not tested on Propagation Delays.

3. This parameter is guaranteed but not tested.

IDT54/74FCT245T/AT/CT FAST CMOS OCTAL BIDIRECTIONAL TRANSCEIVER

TEST CIRCUITS AND WAVEFORMS







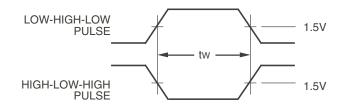
SWITCHPOSITION

Test	Switch
Open Drain Disable Low Enable Low	Closed
All Other Tests	Open

DEFINITIONS:

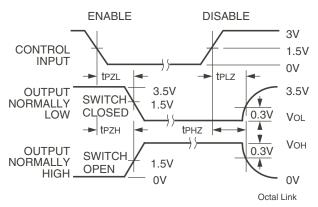
CL = Load capacitance: includes jig and probe capacitance.

RT = Termination resistance: should be equal to Zout of the Pulse Generator.



Pulse Width

Octal Link

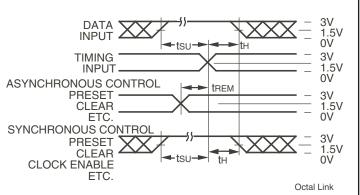


Enable and Disable Times

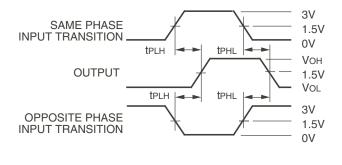
NOTES:

Octal Link

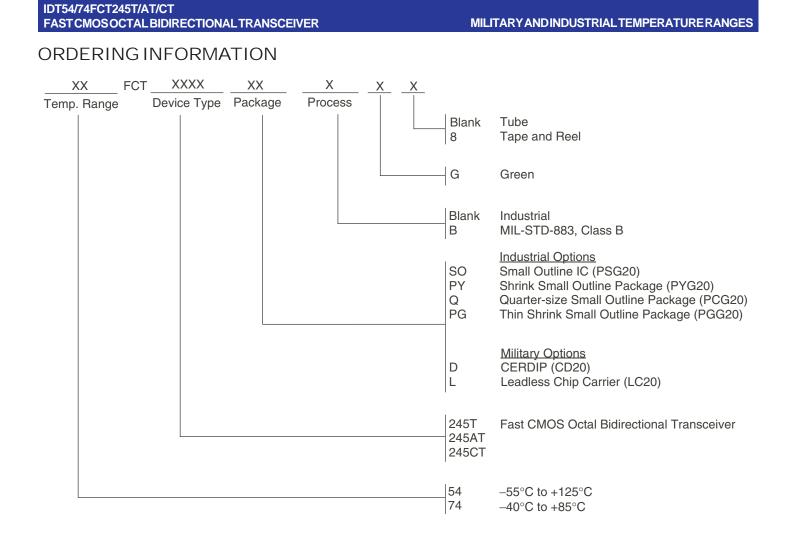
- 1. Diagram shown for input Control Enable-LOW and input Control Disable-HIGH.
- 2. Pulse Generator for All Pulses: Rate \leq 1.0MHz; tF \leq 2.5ns; tR \leq 2.5ns.



Set-Up, Hold, and Release Times



Propagation Delay



Datasheet Document History

09/29/2009Pg. 7Updated the ordering information by removing the "IDT" notation and non RoHS part.12/12/2016Pg. 7Updated the ordering information by adding detailed package information and Tape & Reel.

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